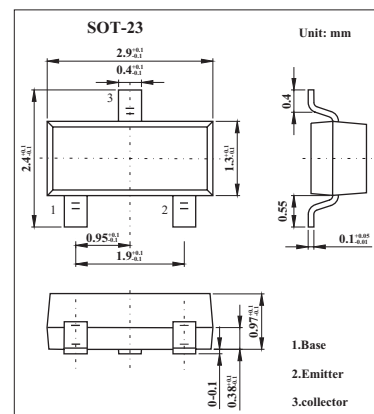


PNP Silicon Epitaxia Transistor

2SA1462

■ Features

- High speed,high voltage switching.
- High f_t : $f_t=1800\text{MHz}$ TYP.
- Low C_{ob} : $C_{ob}=2.0\text{pF}$ TYP.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-15	V
Collector to emitter voltage	V_{CEO}	-15	V
Emitter to base voltage	V_{EBO}	-4.5	V
Collector current	I_C	-50	mA
Total power dissipation $T_a=25^\circ\text{C}$	P_T	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CES}	$V_{CE} = -8.0\text{V}$, $R_{BE}=0$			-100	nA
Emitter cutoff current	I_{EBO}	$V_{EB} = -3.0\text{V}$, $I_C=0$			-100	nA
DC current gain *	h_{FE}	$V_{CE} = -1.0\text{V}$, $I_C = -10\text{mA}$	50	80	150	
		$V_{CE} = -1.0\text{V}$, $I_C = -1\text{mA}$	30	70		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}$, $I_B = -1.0\text{mA}$		-0.09	-0.20	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10\text{mA}$, $I_B = -1.0\text{mA}$		-0.98	-0.95	V
Gain bandwidth product	f_T	$V_{CE} = -10\text{V}$, $I_E = 10\text{mA}$	800	1800		MHz
Output capacitance	C_{ob}	$V_{CB} = -5.0\text{V}$, $I_E = 0$, $f = 1.0\text{MHz}$		2.0	3.0	pF
Turnput Capacitance	t_{on}	$I_C = -10\text{mA}$, $I_{B1} = I_{B2} = -1.0\text{mA}$		9.0	20	ns
Storage Time	t_{stg}			16	40	ns
Turn-off Time	t_{off}			19	40	ns

* Pulse test: $t_p \leq 350 \mu\text{s}$; Duty Cycle $\leq 2\%$

■ h_{FE} Classification

Marking	Y33	Y34
h_{FE}	50~100	75~150